

# HiPerFET™ Power MOSFETs

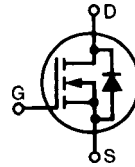
## ISOPLUS247™

IXFR 26N50  
IXFR 24N50

$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
500 V	24 A	0.20 $\Omega$
500 V	22 A	0.23 $\Omega$

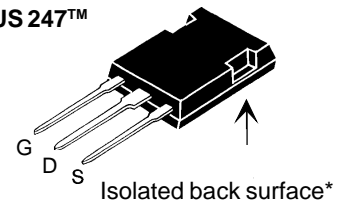
(Electrically Isolated Back Surface)

N-Channel Enhancement Mode  
High  $dV/dt$ , Low  $t_{rr}$ , HDMOS™ Family



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	500	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	26N50	26 A
		24N50	24 A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse width limited by $T_{JM}$	26N50	104 A
		24N50	96 A
$I_{AR}$	$T_C = 25^\circ\text{C}$	26N50	26 A
		24N50	24 A
$E_{AR}$	$T_C = 25^\circ\text{C}$	30	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100\text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$ , $R_G = 2\ \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	250	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ minute leads-to-tab	2500	V~
<b>Weight</b>		6	g

ISOPLUS 247™



G = Gate      D = Drain  
S = Source

\* Patent pending

### Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- -2500V electrical isolation
- Low drain to tab capacitance (<50pF)
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic Rectifier

### Applications

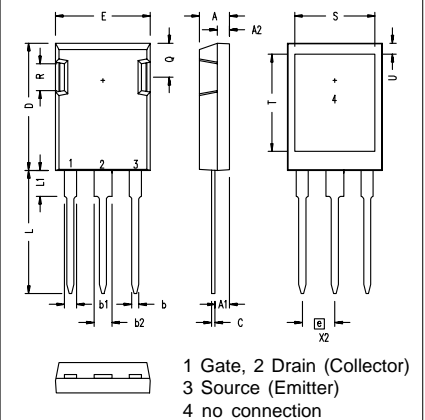
- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

### Advantages

- Easy assembly
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4\text{mA}$	2		V
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100\text{ nA}$
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$		200 $\mu\text{A}$
		$T_J = 125^\circ\text{C}$		1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = I_T$ Notes 1 & 2	26N50		0.20 $\Omega$
		24N50		0.23 $\Omega$

Symbol	Test Conditions	Characteristic Values			
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$			
		min.	typ.	max.	
$g_{fs}$	$V_{DS} = 15\text{ V}; I_D = I_T$ Note 1	11	21	S	
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4200	pF	
$C_{oss}$			450	pF	
$C_{rss}$			135	pF	
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ $R_G = 1\ \Omega$ (External),		16	25	ns
$t_r$			33	45	ns
$t_{d(off)}$			65	80	ns
$t_f$			30	40	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$		135	160	nC
$Q_{gs}$			28	40	nC
$Q_{gd}$			62	85	nC
$R_{thJC}$				0.50	K/W
$R_{thCK}$			0.15		K/W

**ISOPLUS 247 (IXFR) OUTLINE**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	13.21	13.72	.520	.540
T	15.75	16.26	.620	.640
U	1.65	3.03	.065	.080

Source-Drain Diode		Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
Symbol	Test Conditions	min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			26 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			104 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}, \text{ Note 1}$			1.5 V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$	$T_J = 25^\circ\text{C}$		250 ns
$Q_{RM}$		$T_J = 125^\circ\text{C}$		400 ns
		$T_J = 25^\circ\text{C}$	1	1.5 $\mu\text{C}$
$I_{RM}$		$T_J = 125^\circ\text{C}$	2	$\mu\text{C}$
	$T_J = 25^\circ\text{C}$	10	A	
	$T_J = 125^\circ\text{C}$	15	A	

- Note: 1. Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $d \leq 2\%$   
2.  $I_T$  test current: IXFR26N50  $I_T = 13\text{ A}$   
IXFR24N50  $I_T = 12\text{ A}$   
3. See IXFR26N50 data sheet for characteristic curves.

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